EC575 Physics of Semiconductors Devices

Spring Semester 2019

Instructor: Enrico Bellotti Photonics Center, Rm 533 Tel. 617-358-1576 email: bellotti@bu.edu

Class Syllabus

⇒ Part I − Introduction and Review of Quantum Mechanics and Semiconductor Physics

- Review of Quantum Mechanics
- Review of Semiconductor Physics
- Survey of Semiconductor Material Properties.
- Band Structure Calculation Pseudopotential.

⇒ Part II − Carrier Transport Models

- Advanced Carrier Transport Models: BTE
- Drift Diffusion
- Monte Carlo Methods

\Rightarrow Part III - Heterostructures

- Review of p-n junctions.
- p-N and P-n heterostructures

\Rightarrow Part IV - BJT and HBTs

- The Bipolar Junction Transistor: Basic Theory and Limitations.
- The Heterojunction Bipolar Junction Transistor

⇒ Part V – Mesfet, Modulation Doping and HEMTs

- Modulation Doping Fundamentals
- High Electron Mobility Transistor

\Rightarrow Part VI - Photodetectors

- Detection Fundamentals
- Photodiodes and p-i-n detectors
- Avalanche Phototdetectors

\Rightarrow Part VII - Multi-Quantum Wells and Superlattices

- Effective Mass Approximation
- Solution of the Schrödinger equation for the MQW
- Carrier Transport in MQWs
- Real Space Transfer
- Application to RTD and QCs.